## PATENT COOPERATION TREATY

### INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

(Chapter II of the Patent Cooperation Treaty)

(PCT Artcle 36 and Rule 70)

Applicant's or agent's file reference PH-21532-PCT		FOR FURTHER ACTION		See Form PCT/IPEA/416			
International application No. PCT/KR2004/000374		International filing date(date) 24 FEBRUARY 200		Priority date (day/month/) 09 JUNE 2003 (09.06.20			
-	national Patent Classification (IPC			13, 101.12 2003 (03.00.20	/		
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Appl	licant						
РО	STECH FOUNDATION e	t al					
1.	This report is the international pro Authority under Article 35 and tr				amining		
2.	2. This REPORT consists of a total of sheets, including this cover sheet.						
3.	This report is also accompanied by ANNEXES, comprising:  a. (sent to the applicant and to the International Bureau) a total ofsheets, as follows:						
	sheets of the description, claims and/or drawings which have been amended and are the basis for this report and/or sheets containing rectifications authorized by this Authority (see Rule 70.16 and Section 607 of the Administrative Instructions).						
		•	nich this Authority con	siders contain an amendmen	nt that goes		
	sheets which supersede earlier sheets, but which this Authority considers contain an amendment that goes beyond the disclosure in the international application as filed, as indicated in item 4 of Box No. I and the						
	Supplemental Box.  b. (sent to the International Bureau only) a total of (indicate type and number of electronic carrier(s))						
	containing a sequence listing and/or tables related thereto, in computer readable form only, as indicated in the						
	Supplemental Box relating to Sequence Listing (see Section 802 of the Administrative Instructions).						
4.	4. This report contains indications relating to the following items:						
"	Box No. 1 Basis of the report						
	Box No. II Priority						
Box No. III Non-establishment of opinion with regard to novelty, inventive step and industrial applicability				ability			
-	Box No. 1V Lack of unity of invention						
1	Box No. V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement				ial applicability;		
	Box No. VI Certain documents cited						
	Box No. VII Certain defects in the international application						
	Box No. VIII Certain observations on the international application						
Date	e of submission of the demand		Date of completion o	f this report			
	06 JANUARY 2005	(06.01.2005)	27 SEPTEM	IBER 2005 (27.09.2005)			
Nan	ne and mailing address of the IPEA	/KR	Authorized officer		MARINE		
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Face	simile No. 82-42-472-7140		Telephone No. 82-4	12-481-5749	All light		

# INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

International application No. PCT/KR2004/000374

Во	x No.	. 1 Basis of the report		
1.		th regard to the language, this report is based on the international aperwise indicated under this item.  This report is based on translations from the original language interwhich is the language of a translation furnished for the purposes of international search (under Rules 12.3 and 23.1(b))  publication of the international application (under Rules 12. international preliminary examination (under Rules 55.2 and	o the following language f:	
2.	to th	n regard to the elements of the international application, this report is receiving Office in response to an invitation under Article 14 are a exed to this report):  the international application as originally filed/furnished		-
			as is Authority onas	originally filed/furnished
		pages* received by the drawings:  pages pages received by the drawings:  pages received by the drawings:	amended (together with any sais Authority onas oneas one of the Authority onas one of the Authority on	originally filed/furnished statment) under Article 19
		the sequence listing and/or any related table(s) - see Supplemental		ing.
3.		The amendments have resulted in the cancellation of:  the description, pages the claims, Nos. the drawings, sheets the sequence listing (specify):  any table(s) related to sequence listing (specify):		
4.		This report has been established as if (some of) the amendments a made, since they have been considered to go beyond the disclosur (Rule 70.2(c)).  the description, pages the claims, Nos. the drawings, sheets the sequence listing (specify): any table(s) related to sequence listing (specify):	e as filed, as indicated in the S	upplemental Box
* ,	If iten	n 4 applies, some or all of those sheets may be marked "superseded.	n	

### INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

International application No. PCT/KR2004/000374

Box No. V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement

1. Statement			
Novelty (N)	Claims	1-15	YES
	Claims	NONE	NO
Inventive step (IS)	Claims	7-8, 14-15	YES
	Claims	1-6, 9-13	NO
Industrial applicability (IA)	Claims	1-15	YES
	Claims	NONE	ОИ

- 2. Citations and explanations (Rule 70.7)
  - (1) The documents cited in the International Search Report are as follows:

D1: KR 2003-85272 A

D2: JP 2003-73859 A

D3: WO 94/00885 A1

D4: JP 2003-45661 A

D5: JP 2000-31462 A

### .(2) Novelty

The subject-matter of claims 1-15 is considered to be new under PCT Article 33(2).

### (3) Inventive Step

### Claims 1-6

The subject-matter of claims 1-6 is about a contact fabric using a heterostructure of metal/semiconductor nanorods comprising: semiconductor nanorods; and metals deposited on semiconductor nanorods wherein there is a low contact resistance ohmic characteristic or a rectifying Schottky characteristic between the nanorods and the metals

D2 discloses a regularly arranged nano-structure(7) joined on the substrate(1). The substance forming the nano-structure such as TiO₂ or ZnO can develop photocatalyst characteristics when absorbing at least ultraviolet radiation or the ultra-violet of sun light. The regularly arranged nano-structure is obtained on the substrate, which has a morphology such as nanotube, nanodot, nano drill rod, nano fiber, and nano wire. (the abstract, figures 1, 2 of D1)

D3 discloses a light emitting device incorporating a layer of porous silicon of low dimensionality surmounted by a discontinuous layer of silver in the form of discrete islands. A digitated electrode is connected to the islands, and the islands have diameters in the range of 5 nm to 20 nm and spacings in the range of 10 nm to 50 nm. They form a Schottky diode structure on the silicon. ( the abstract of D2)

Therefore, the technical features of claims 1-6 are already disclosed in D2 and D3 in a similar field of application, or are included among several straightforward possibilities or combinations from which the skilled person could select without the exercise of inventive skill.

-continued-

#### INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

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#### Supplemental Box

In case the space in any of the preceding boxes is not sufficient. Continuation of:

BOX V.

### Claims 9-13

The subject-matter of claims 9-13 is about a method for manufacturing a contact fabric using a heterostructure of metal/semiconductor nanorods. The method comprises a step for making a nanorods, and a step for depositing metals on the nanorods, wherein there is a low contact resistance ohmic characteristic or a rectifying Schottky characteristics between the nanorods and the metals.

D2 discloses a manufacturing method of a regularly arranged nano-structure joined on the substrate. The substance for forming the nano-structure, the size and the distribution of nanorods, the substance of electrodes, and the characteristic of nanorods are disclosed in D2.

D3 discloses a manufacturing method of a light emitting device incorporating a layer of porous silicon of low dimensionality surmounted by a discontinuous layer of silver in the form of discrete islands. A digitated electrode is connected to the islands, and the islands have diameters in the range of 5 nm to 20 nm. The nanorods form Schottky diode structures on the silicon.

Therefore, the features of 9-13 are already disclosed in D2 and D3 in a similar field of application, or are included among several straightforward possibilities or combinations from which the skilled person could select without the exercise of inventive skill.

Consequently, the subject-matter of claims 1-6, 9-13 lacks an inventive step under PCT Article 33(3)

### Claims 7-8 and 14-15

The subject-matter of Claims 7 and 14 is about a contact fabric and a method for manufacturing a contact fabric containing Au or Pt layer formed on the metal layer.

And the subject-matter of Claims 8 and 15 is about a contact fabric which is heat treated for the development of the electrical characteristic and a method for manufacturing a contact fabric containing an extra heat treatment step.

But none of the documents D1-D5 refer to the above-mentioned technical features.

Consequently, the subject-matter of claims 7-8 and 14-15 is believed to have an inventive step under PCT Article 33(3).

### (4) Industrial Applicability

The subject matter of Claims 1-15 is considered to be industrially applicable under PCT Article 33(4).